

B1  
Cmt

1) said observation part includes a first MOS transistor having:

i) a source/drain region including a first impurity region of a first conductivity type, that is connected with said first end of said wire and that is formed within a second impurity region of a second conductivity type; and

ii) a gate electrode that is electrically insulated from a gate electrode of said second MOS transistor; and

2) said pn junction includes said first and second impurity regions.

B2

6. (Twice Amended) The semiconductor device according to claim 1, wherein:

said portion measured is said gate electrode of said second MOS transistor.

B3

Sub  
C1

11. (Twice Amended) The semiconductor device according to claim 1, wherein:

a) said first conductivity type is an n type and said second conductivity type is a p type;

b) said observation part further includes:

1) a second pn junction having a p-type third impurity region connected with said wire; and an n-type fourth impurity region; and

c) a first fixed potential is applied to said second impurity region and a second fixed potential higher than said first fixed potential is applied to said fourth impurity region.

#### REMARKS

Favorable reconsideration of the above-identified patent application in light of the foregoing amendment and the following remarks is respectfully requested.

**STATUS.** Claims 1, 6-7, and 11 remain active in the application. Claims 1, 6, and 11 have been amended by way of the present amendment.

**THE JULY 2, 2002 OFFICE ACTION.** In the Office Action dated July 3, 2002, the restriction requirement was made final; FIG. 11 was objected to as not being labeled "Prior Art";